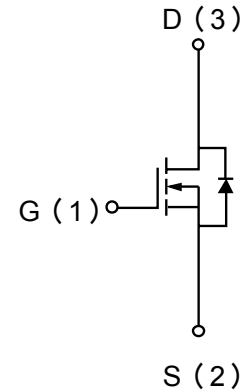


**Description**

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
$V_{DS}(V)$	$R_{DS(on)}(\Omega)$	$I_D(A)$
30	0.030@ $V_{GS}=10V$	5.8


**Electrical characteristics per line@25°C ( unless otherwise specified)**

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	30		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 12V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.7		1.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5.8A$	-	0.030	0.040	$\Omega$
		$V_{GS} = 4.5V, I_D = 5A$	-	0.040	0.048	$\Omega$
		$V_{GS} = 2.5V, I_D = 4A$	-	0.050	0.058	$\Omega$
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	$C_{ISS}$	$V_{GS} = 0V, V_{DS} = 15V,$ $f = 1MHz$	-	800		pF
Output Capacitance	$C_{DSS}$		-	100		pF
Reverse Transfer Capacitance	$C_{RSS}$		-	80		pF
<b>SWITCHING PARAMETERS</b>						
Turn-On Delay Time	$t_{d(on)}$	$V_{DS} = 15V, V_{GS} = 10V,$ $R_G = 10\Omega,$ $I_D = 0.2A$	-		5	ns
Turn-Off Delay Time	$t_{d(off)}$		-		40	ns

Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	$\pm 12$	V
Drain Current	Continuous	$I_D$	5.8	A
	Pulsed	$I_D$	30	A
Total Power Dissipation	$T_A=25^\circ\text{C}$	$P_D$	1.4	W
	$T_A=70^\circ\text{C}$	$P_D$	1	W

Typical Characteristics

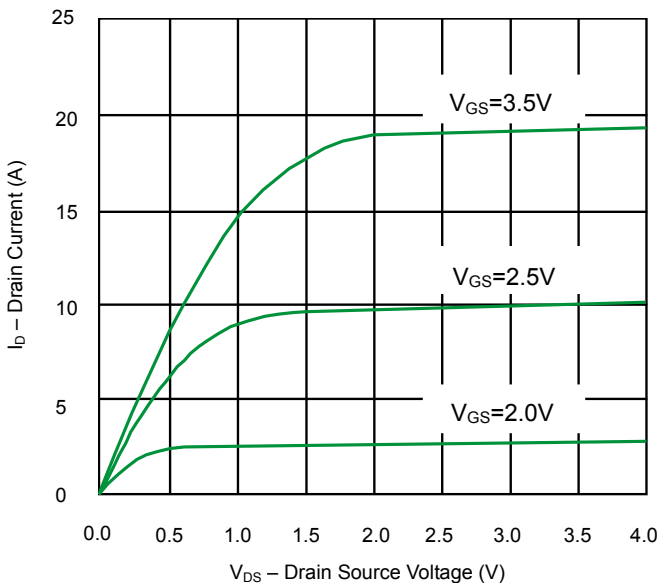


Fig 1. Output Characteristics

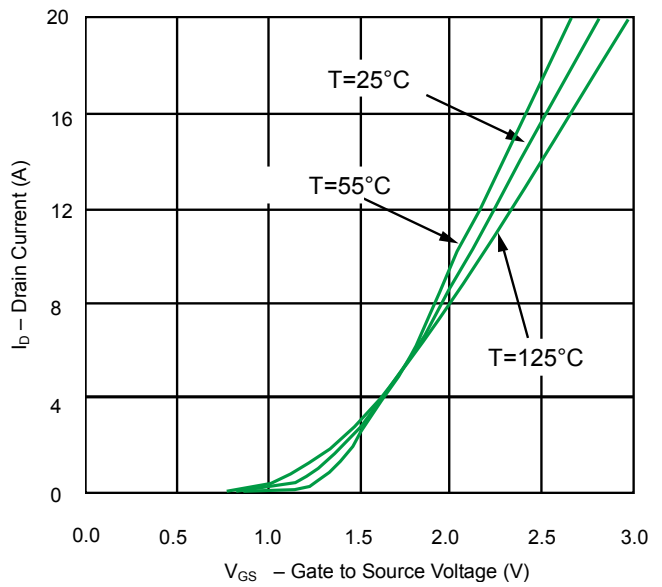


Fig 2. Transfer Characteristics

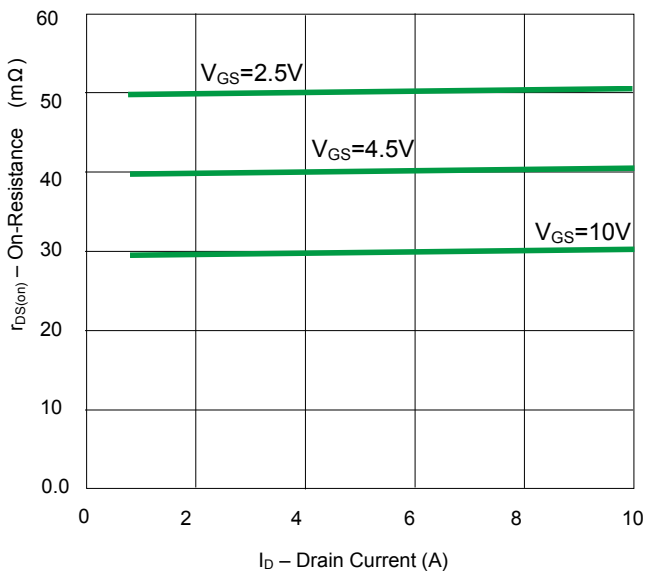


Fig 3. Drain-Source On-Resistance

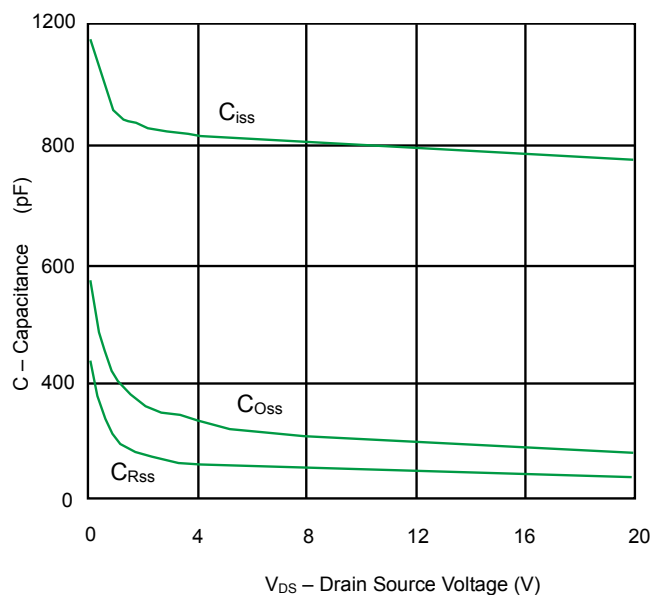
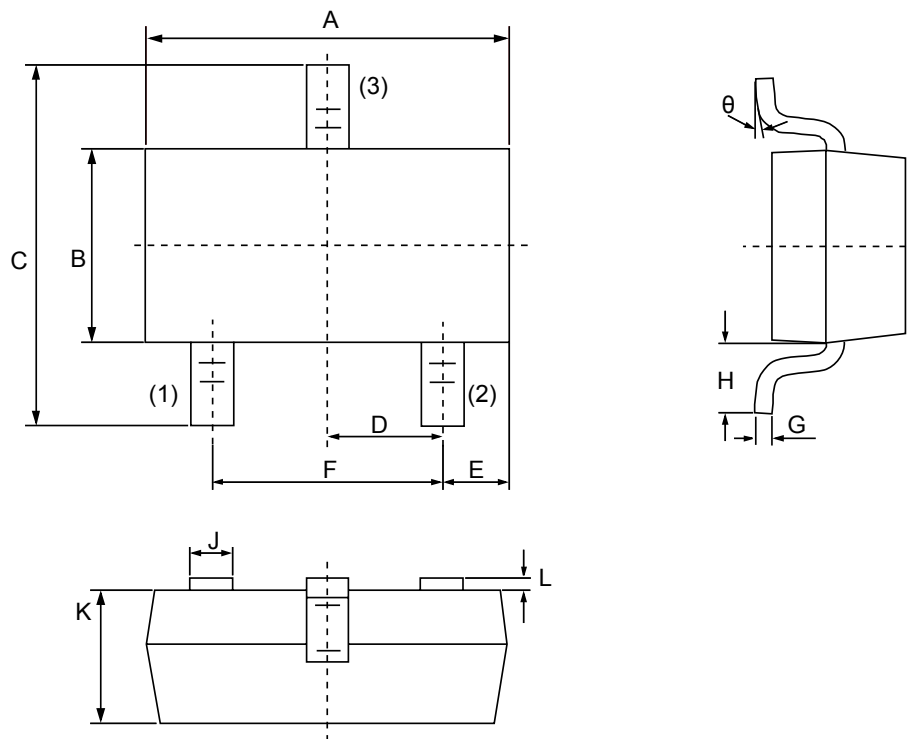



Fig 4. Capacitance

Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°


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